SCES131C - MARCH 1998 - REVISED JULY 1998

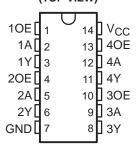
- EPIC<sup>™</sup> (Enhanced-Performance Implanted CMOS) Process
- Typical V<sub>OLP</sub> (Output Ground Bounce)
  < 0.8 V at V<sub>CC</sub>, T<sub>A</sub> = 25°C
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot)
  > 2 V at V<sub>CC</sub>, T<sub>A</sub> = 25°C
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (D, NS), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages, Ceramic Flat (W) Packages, Chip Carriers (FK), and DIPs (J)

#### description

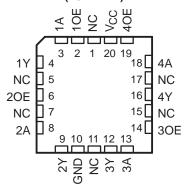
These quadruple bus buffer gates are designed for 2-V to 5.5-V  $V_{CC}$  operation.

The 'LV126A devices feature independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (OE) input is low.

SN54LV126A . . . J OR W PACKAGE SN74LV126A . . . D, DB, DGV, NS, OR PW PACKAGE (TOP VIEW)



SN54LV126A . . . FK PACKAGE (TOP VIEW)



NC - No internal connection

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The SN54LV126A is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74LV126A is characterized for operation from –40°C to 85°C.

## FUNCTION TABLE (each buffer)

INPU	JTS	OUTPUT
OE	Α	Υ
Н	Н	Н
Н	L	L
L	Χ	Z



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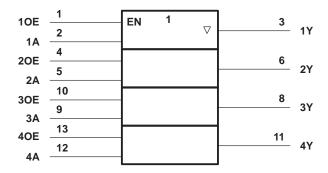
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### SN54LV126A, SN74LV126A QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

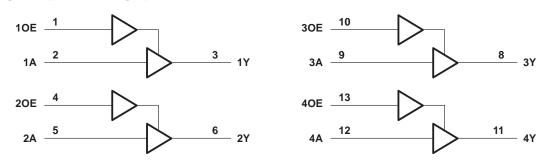
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#### logic symbol<sup>†</sup>



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the D, DB, DGV, J, NS, PW, and W packages.

#### logic diagram (positive logic)



Pin numbers shown are for the D, DB, DGV, J, NS, PW, and W packages.

### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V <sub>CC</sub>		–0.5 V to 7 V
Input voltage range, V <sub>I</sub> (see Note 1)		0.5 V to 7 V
Output voltage range, VO (see Notes 1 and 2)		0.5 V to V <sub>CC</sub> + 0.5 V
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)		–20 mA
Output clamp current, IOK (VO < 0 or VO > VC	c)	±50 mA
Continuous output current, $I_O$ ( $V_O = 0$ to $V_{CC}$ )	-	±35 mA
Continuous current through V <sub>CC</sub> or GND		±70 mA
Package thermal impedance, θ <sub>JA</sub> (see Note 3)	: D package	127°C/W
	DB package	158°C/W
	DGV package	182°C/W
	NS package	127°C/W
	PW package	170°C/W
Operating free-air temperature range, T <sub>A</sub>		–40°C to 85°C
Storage temperature range, T <sub>sta</sub>		–65°C to 150°C

<sup>‡</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

- 2. This value is limited to 7 V maximum.
- 3. The package thermal impedance is calculated in accordance with JESD 51.



#### recommended operating conditions (see Note 4)

			SN54LV	126A	SN74LV	126A	UNIT
			MIN	MAX	MIN	MAX	ONII
Vcc	Supply voltage		2	5.5	2	5.5	V
		V <sub>CC</sub> = 2 V	1.5		1.5		
VIH	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	V <sub>CC</sub> × 0.7		$V_{CC} \times 0.7$		V
٧IH	r light-level lilput voltage	$V_{CC} = 3 V \text{ to } 3.6 V$	V <sub>CC</sub> × 0.7		$V_{CC} \times 0.7$		ľ
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	V <sub>CC</sub> ×0.7		$V_{CC} \times 0.7$		
		V <sub>CC</sub> = 2 V		0.5		0.5	
٧	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	V	CC × 0.3	V	CC × 0.3	V
VIL	Low-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V	V	CC × 0.3	V	CC × 0.3	1 °
		V <sub>CC</sub> = 4.5 V to 5.5 V	V	CC × 0.3	V	CC × 0.3	1
٧ <sub>I</sub>	Input voltage	-	0	5.5	0	5.5	V
1/-	Output valtage	High or low state	0 4	Vcc	0	Vcc	V
VO	Output voltage	3-state	0 2	5.5	0	5.5	1 °
		V <sub>CC</sub> = 2 V	20	-50		-50	μΑ
la	High lovel output ourrent	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	30	-2		-2	·
ЮН	High-level output current	V <sub>CC</sub> = 3 V to 3.6 V	Q	-8		-8	mA
		V <sub>CC</sub> = 4.5 V to 5.5 V		-16		-16	1
		V <sub>CC</sub> = 2 V		50		50	μΑ
la.	Loughous output ourrest	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2		2	
IOL	Low-level output current	V <sub>CC</sub> = 3 V to 3.6 V		8		8	mA
		V <sub>CC</sub> = 4.5 V to 5.5 V		16		16	1
		V <sub>CC</sub> = 2.3 V to 2.7 V	0	200	0	200	
$\Delta t/\Delta v$	Input transition rise or fall rate	V <sub>CC</sub> = 3 V to 3.6 V	0	100	0	100	ns/V
		V <sub>CC</sub> = 4.5 V to 5.5 V	0	20	0	20	]
TA	Operating free-air temperature		-55	125	-40	85	°C

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST SOMBITIONS		SN5	4LV126	6A	SN7	4LV126	SA S	
PARAMETER	TEST CONDITIONS	Vcc	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
	I <sub>OH</sub> = -50 μA	2 V to 5.5 V	V <sub>CC</sub> -0.1	1		V <sub>CC</sub> -0.1			
V	$I_{OH} = -2 \text{ mA}$	2.3 V	2			2			V
VOH	$I_{OH} = -8 \text{ mA}$	3 V	2.48			2.48			V
	I <sub>OH</sub> = -16 mA	4.5 V	3.8		3	3.8			
	I <sub>OL</sub> = 50 μA	2 V to 5.5 V		Ş	0.1			0.1	
Va	$I_{OL} = 2 \text{ mA}$	2.3 V		0,00	0.4			0.4	V
VOL	$I_{OL} = 8 \text{ mA}$	3 V		5	0.44			0.44	V
	I <sub>OL</sub> = 16 mA	4.5 V	200	5	0.55			0.55	
lį	$V_I = V_{CC}$ or GND	5.5 V	60%		±1			±1	μΑ
loz	$V_O = V_{CC}$ or GND	5.5 V	Q.		±5			±5	μΑ
ICC	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			20			20	μΑ
l <sub>off</sub>	$V_I$ or $V_O = 0$ to 5.5 $V$	0 V			5			5	μΑ
C <sub>i</sub>	$V_I = V_{CC}$ or GND	3.3 V		1.6			1.6		pF

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### SN54LV126A, SN74LV126A QUADRUPLE BUS BUFFER GATES WITH 3-STATE OUTPUTS

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# switching characteristics over recommended operating free-air temperature range, $V_{CC}$ = 2.5 V $\pm$ 0.2 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	то	LOAD	T,	<b>Վ = 25°</b> C	;	SN54L	/126A	SN74L\	/126A	UNIT
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
t <sub>pd</sub> *	А	Υ			7.1	13	1	15.5	1	15.5	
t <sub>en</sub> *	OE	Υ	C <sub>L</sub> = 15 pF		7.4	13	1	15.5	1	15.5	ns
<sup>t</sup> dis*	OE	Υ			5.7	14.7	1	17	1	17	
<sup>t</sup> pd	А	Υ			9.2	16.5	1/	18.5	1	18.5	
t <sub>en</sub>	OE	Υ	C 50 pE		9.5	16.5	77	18.5	1	18.5	no
<sup>t</sup> dis	OE	Y	C <sub>L</sub> = 50 pF		8.1	18.2	15	20.5	1	20.5	ns
t <sub>sk(o)</sub> †						2	0			2	

<sup>\*</sup> On products compliant to MIL-PRF-38535, this parameter is not production tested.

# switching characteristics over recommended operating free-air temperature range, $V_{CC}$ = 3.3 V $\pm$ 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	DAMETER FROM TO LO		FROM TO LOAD TA = 25°C		;	SN54L	/126A	SN74L\	UNIT		
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
t <sub>pd</sub> *	А	Υ			5	8	1	9.5	1	9.5	
t <sub>en</sub> *	OE	Υ	C <sub>L</sub> = 15 pF		5.1	8	1	9.5	1	9.5	ns
<sup>t</sup> dis*	OE	Υ			4.4	9.7	1	11.5	1	11.5	
<sup>t</sup> pd	А	Υ			6.4	11.5	1/	13	1	13	
t <sub>en</sub>	OE	Υ	C 50 pE		6.6	11.5	) <sub>77(</sub>	13	1	13	no
<sup>t</sup> dis	OE	Υ	C <sub>L</sub> = 50 pF		6.1	13.2	0 1	15	1	15	ns
t <sub>sk(o)</sub> †						1.5	Q			1.5	

<sup>\*</sup> On products compliant to MIL-PRF-38535, this parameter is not production tested.

# switching characteristics over recommended operating free-air temperature range, $V_{CC}$ = 5 V $\pm$ 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	FROM TO LO		T,	T <sub>A</sub> = 25°C		SN54LV126A		SN74L\	/126A	UNIT
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
tpd*	А	Υ			3.5	5.5	1	6.5	1	6.5	
t <sub>en</sub> *	OE	Y	C <sub>L</sub> = 15 pF		3.6	5.1	1	6	1	6	ns
<sup>t</sup> dis*	OE	Y			3.3	6.8	1	8	1	8	
<sup>t</sup> pd	А	Y			4.6	7.5	1/	8.5	1	8.5	
t <sub>en</sub>	OE	Y	C 50 pE		4.6	7.1	) <sub>77</sub> (	8	1	8	no
<sup>t</sup> dis	OE	Y	C <sub>L</sub> = 50 pF		4.3	8.8	0 1	10	1	10	ns
t <sub>sk(o)</sub> †						1	Q			1	

<sup>\*</sup> On products compliant to MIL-PRF-38535, this parameter is not production tested.

<sup>†</sup> Skew between any two outputs of the same package switching in the same direction

<sup>†</sup> Skew between any two outputs of the same package switching in the same direction

<sup>†</sup> Skew between any two outputs of the same package switching in the same direction

## noise characteristics, $V_{CC}$ = 3.3 V, $C_L$ = 50 pF, $T_A$ = 25°C (see Note 5)

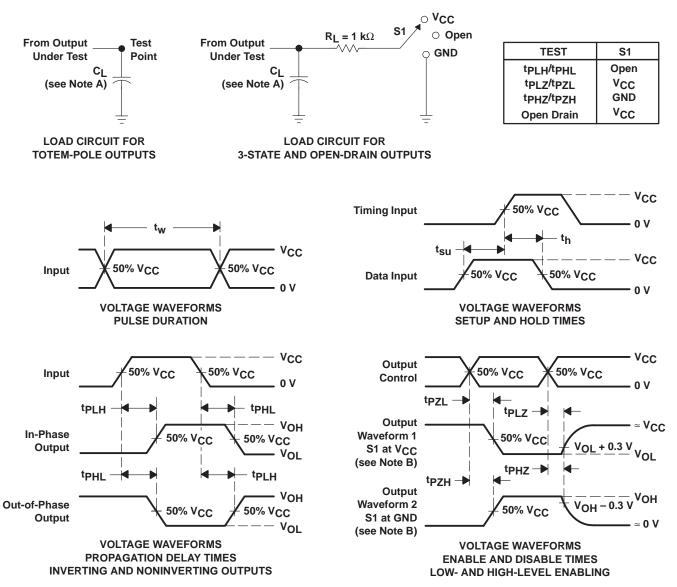
	PARAMETER	SN	UNIT		
	PARAMETER	MIN	TYP	MAX	UNIT
V <sub>OL(P)</sub>	Quiet output, maximum dynamic V <sub>OL</sub>		0.32	0.8	V
V <sub>OL(V)</sub>	Quiet output, minimum dynamic VOL		-0.23	-0.8	V
VOH(V)	Quiet output, minimum dynamic VOH		3.06		V
V <sub>IH(D)</sub>	High-level dynamic input voltage	2.31			V
V <sub>IL(D)</sub>	Low-level dynamic input voltage			0.97	V

NOTE 5: Characteristics are for surface-mount packages only.

### operating characteristics, $T_A = 25^{\circ}C$

PARAMETER			TEST CO	VCC	TYP	UNIT	
Card	Power dissinction conscitance	Outpute enabled	C 50 pE	f = 10 MHz	3.3 V	14.4	pF
Cpd	Power dissipation capacitance	Outputs enabled	C <sub>L</sub> = 50 pF,	1 = 10 WITZ	5 V	15.9	þг

#### PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C<sub>I</sub> includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O = 50 \Omega$ ,  $t_f \leq 3$  ns.  $t_f \leq 3$  ns.
  - D. The outputs are measured one at a time with one input transition per measurement.
  - E. tpLZ and tpHZ are the same as tdis.
  - F. tpzL and tpzH are the same as ten.
  - G. tpHI and tpI H are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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